

MMBFU310LT1

Preferred Device

JFET Transistor

N-Channel

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Gate-Source Voltage	V_{GS}	25	Vdc
Gate Current	I_G	10	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

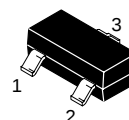
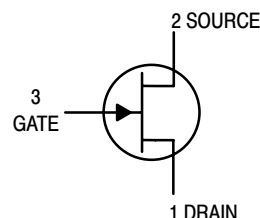
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



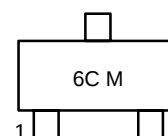
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236AB)
CASE 318-08
STYLE 10

MARKING DIAGRAM



6C = Specific Device Code
M = Date Code
▪ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBFU310LT1	SOT-23	3000 Tape & Reel
MMBFU310LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBFU310LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Gate-Source Breakdown Voltage - ($I_G = -1.0 \mu\text{Adc}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	-25	-	Vdc
Gate 1 Leakage Current - ($V_{GS} = -15 \text{ Vdc}$, $V_{DS} = 0$)	I_{G1SS}	-	-150	pA
Gate 2 Leakage Current - ($V_{GS} = -15 \text{ Vdc}$, $V_{DS} = 0$, $T_A = 125^\circ\text{C}$)	I_{G2SS}	-	-150	nAdc
Gate Source Cutoff Voltage - ($V_{DS} = 10 \text{ Vdc}$, $I_D = 1.0 \text{ nAdc}$)	$V_{GS(off)}$	-2.5	-6.0	Vdc

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current - ($V_{DS} = 10 \text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	24	60	mAdc
Gate-Source Forward Voltage - ($I_G = 10 \text{ mAdc}$, $V_{DS} = 0$)	$V_{GS(f)}$	-	1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance - ($V_{DS} = 10 \text{ Vdc}$, $I_D = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	$ Y_{fs} $	10	18	mmhos
Output Admittance - ($V_{DS} = 10 \text{ Vdc}$, $I_D = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	$ y_{os} $	-	250	μmhos
Input Capacitance - ($V_{GS} = -10 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{iss}	-	5.0	pF
Reverse Transfer Capacitance - ($V_{GS} = -10 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{rss}	-	2.5	pF

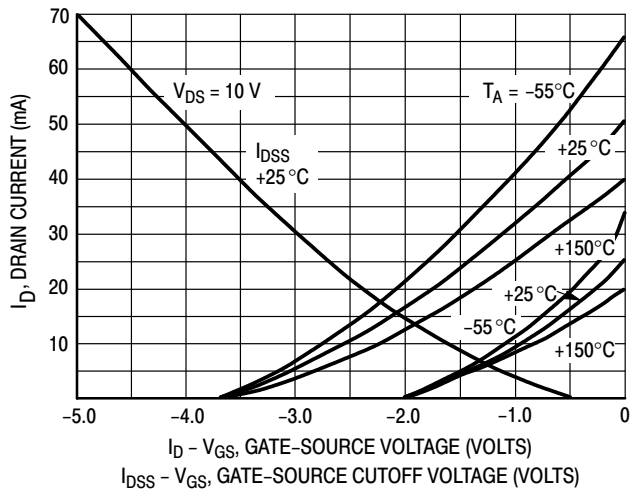


Figure 1. Drain Current and Transfer Characteristics vs Gate-Source Voltage

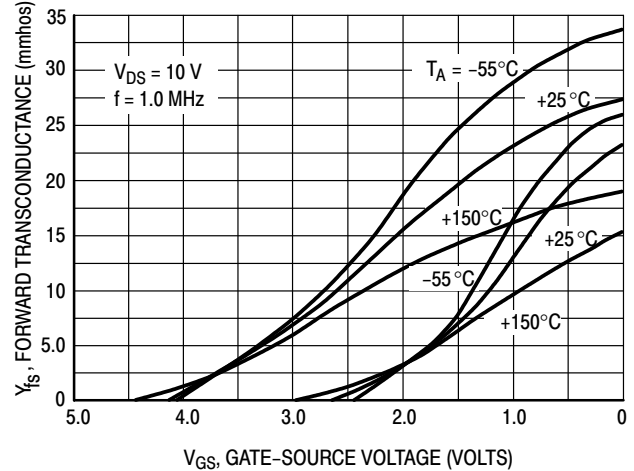


Figure 2. Forward Transconductance vs Gate-Source Voltage

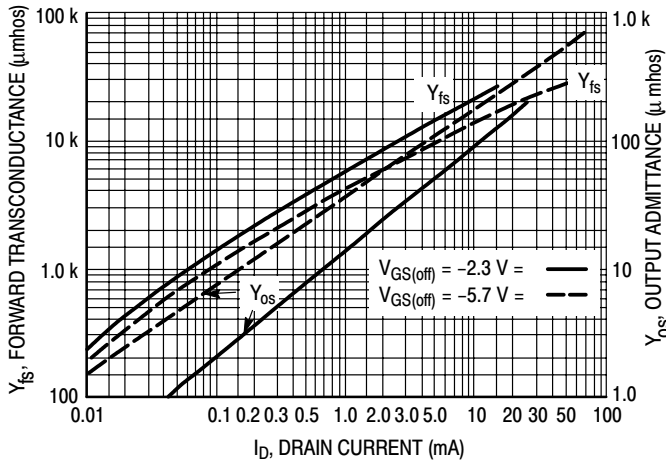


Figure 3. Common-Source Output Admittance and Forward Transconductance vs Drain Current

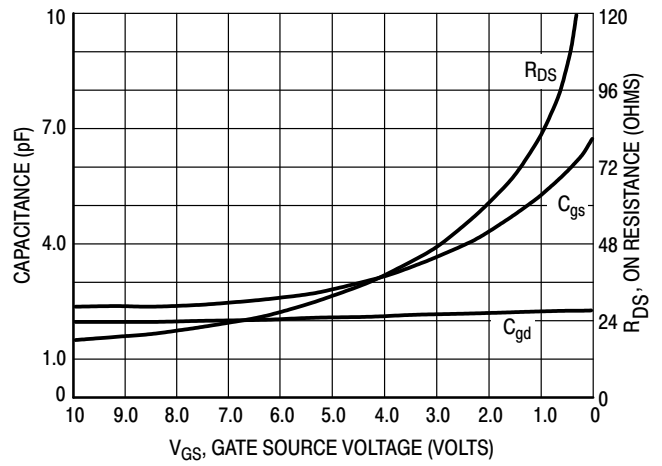


Figure 4. On Resistance and Junction Capacitance vs Gate-Source Voltage

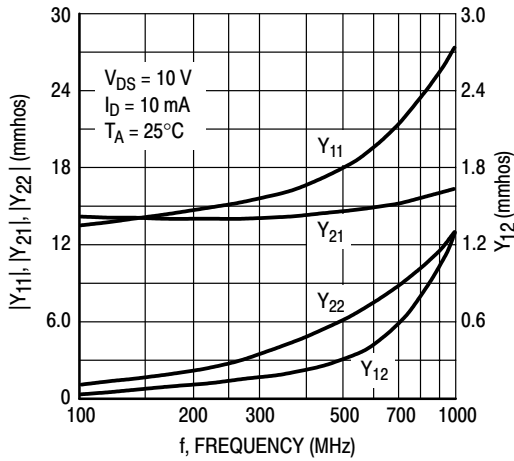


Figure 5. Common-Gate Y Parameter Magnitude vs Frequency

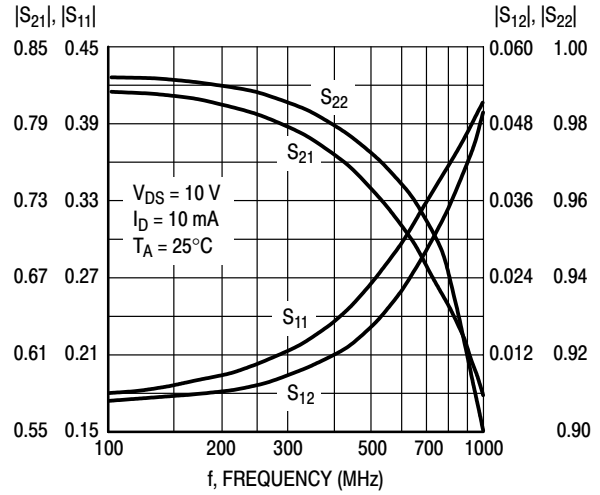


Figure 6. Common-Gate S Parameter Magnitude vs Frequency

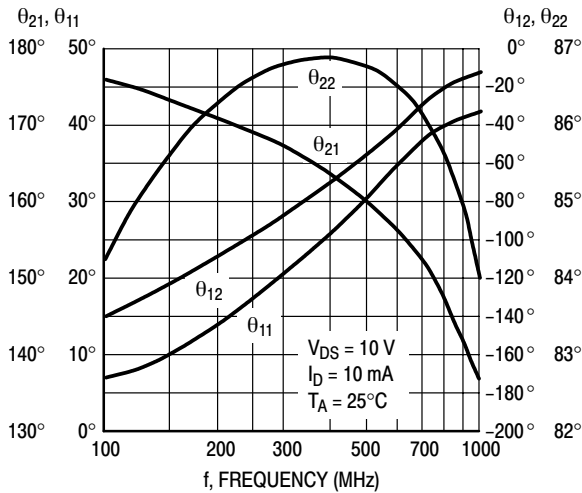


Figure 7. Common-Gate Y Parameter Phase-Angle vs Frequency

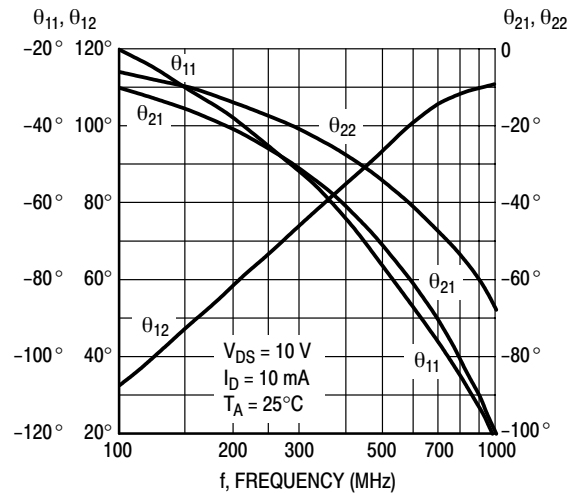
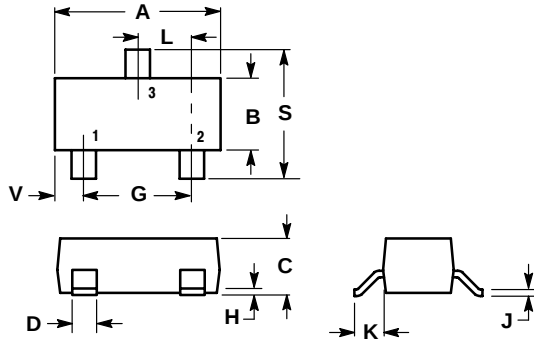


Figure 8. S Parameter Phase-Angle vs Frequency

MMBFU310LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236AB) CASE 318-08 ISSUE AH



NOTES:

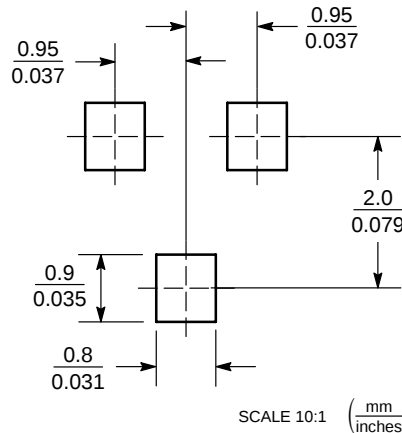
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 10:

1. DRAIN
2. SOURCE
3. GATE

SOLDERING FOOTPRINT*



SCALE 10:1 (mm / inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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